

Complementary power Darlington transistors

Features

- Good h_{FE} linearity
- High f_T frequency
- Monolithic Darlington configuration with integrated antiparallel collector-emitter diode

Application

- Linear and switching industrial equipment

Description

The devices are manufactured in planar technology with “base island” layout and monolithic Darlington configuration.

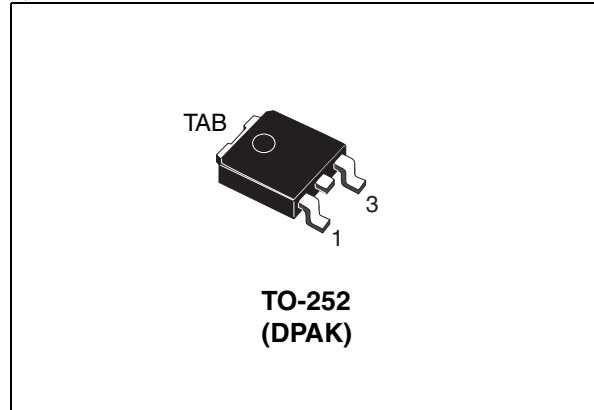


Figure 1. Internal schematic diagram

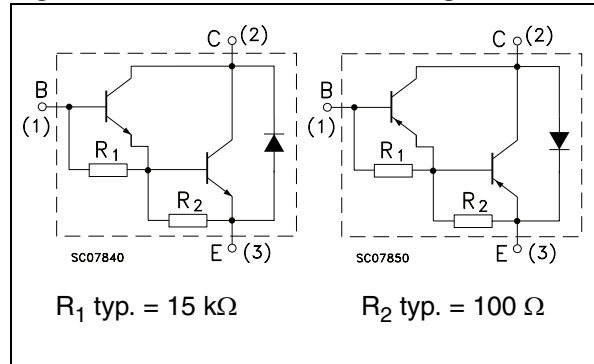


Table 1. Device summary

Order codes	Marking	Polarity	Package	Packaging
MJD112T4	MJD112	NPN	DPAK	Tape and reel
MJD117T4	MJD117	PNP	DPAK	Tape and reel

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	100	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)		
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I_C	Collector current	2	A
I_{CM}	Collector peak current	4	A
I_B	Base current	0.05	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ °C}$	20	W
T_{STG}	Storage temperature	-65 to 150	°C
T_J	Max. operating junction temperature	150	°C

Note: For PNP types voltage and current values are negative.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case max.	6.25	°C/W

2 Electrical characteristics

$T_{\text{case}} = 25\text{ °C}$; unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CEV}	Collector cut-off current ($V_{\text{BE}} = -1.5\text{ V}$)	$V_{\text{CE}} = 80\text{ V}$ $V_{\text{CE}} = 80\text{ V}, T_c = 125\text{ °C}$		-	10 0.5	μA mA
I_{CBO}	Collector cut-off current ($I_E = 0$)	$V_{\text{CB}} = 80\text{ V}$ $V_{\text{CB}} = 100\text{ V}$		-	10 20	μA
I_{CEO}	Collector cut-off current ($I_B = 0$)	$V_{\text{CE}} = 50\text{ V}$		-	20	μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{\text{EB}} = 5\text{ V}$		-	2	mA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ($I_B = 0$)	$I_C = 30\text{ mA}$	100	-		V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_C = 2\text{ A}$ $I_B = 8\text{ mA}$		-	2	V
		$I_C = 4\text{ A}$ $I_B = 40\text{ mA}$		-	3	
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_C = 4\text{ A}$ $I_B = 40\text{ mA}$		-	4	V
$V_{\text{BE(on)}}$	Base-emitter on voltage	$I_C = 2\text{ A}$ $V_{\text{CE}} = 3\text{ V}$		-	2.8	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_C = 0.5\text{ A}$ $V_{\text{CE}} = 3\text{ V}$	500	-		
		$I_C = 2\text{ A}$ $V_{\text{CE}} = 3\text{ V}$	1000	-	12000	
		$I_C = 4\text{ A}$ $V_{\text{CE}} = 3\text{ V}$	200	-		
f_T	Transition frequency	$I_C = 0.75\text{ A}$ $V_{\text{CE}} = 10\text{ V}$ $f = 1\text{ MHz}$	25	-		MHz
C_{CBO}	Collector base capacitance ($I_E = 0$)	$V_{\text{CB}} = 10\text{ V}$ $f = 0.1\text{ MHz}$		-	100	pF
		for MJD112 for MJD117			200	pF

1. Pulse test: pulse duration $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

Note: For PNP types voltage and current values are negative.

2.1 Typical characteristic (curves)

Figure 2. DC current gain
($V_{CE} = 3\text{ V NPN}$)

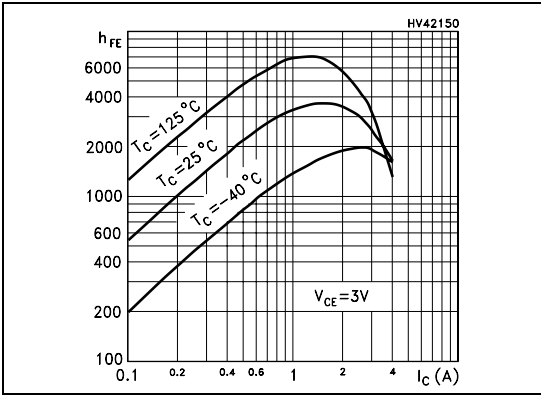


Figure 3. DC current gain
($V_{CE} = -3\text{ V PNP}$)

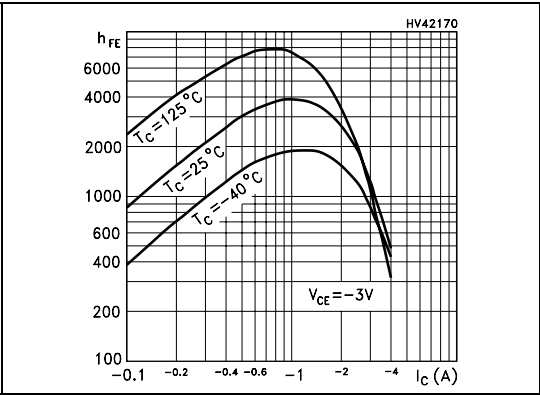


Figure 4. DC current gain
($V_{CE} = 5\text{ V NPN}$)

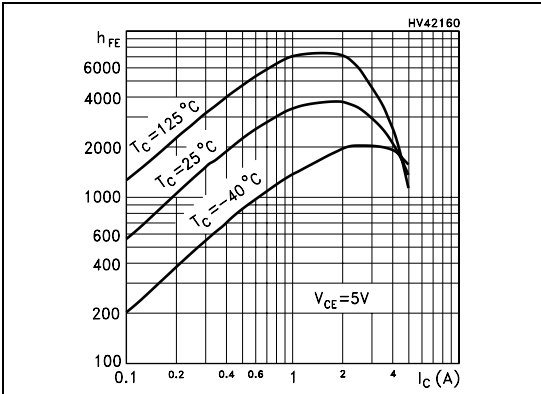


Figure 5. DC current gain
($V_{CE} = -5\text{ V PNP}$)

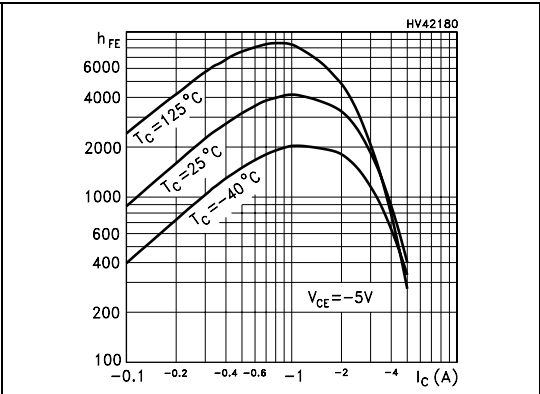


Figure 6. Collector-emitter saturation
voltage (NPN)

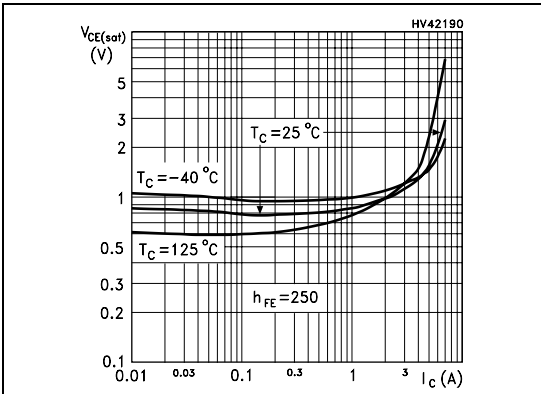


Figure 7. Collector-emitter saturation
voltage (PNP)

